IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Application No.: Date Filed: Title:		Srikanth B. Samavedam	Group Art Unit: Examiner:						
		METHOD OF FORMING A THEREOF	METHOD OF FORMING AN NMOS TRANSISTOR AND STRUCTURE THEREOF						
		INFORMATION DISC	LOSURE STATEMENT (IDS)						
	ssioner F Iria, VA	or Patents 22313							
SIR:									
States P for subrepatent a	n attache atent and nitting a pplicatio	d Form PTO/SB/08 and/or subsequal Trademark Office. Pursuant to the copy of each cited U.S. patent and one filed after June 30, 2003 and for	compliance with 37 C.F.R. §§1.97 and 1.98, the references tently identified herein, are for consideration by the United Office waiving the requirement under 37 CFR 1.98 (a)(2)(i) each U.S. patent application publication for all U.S. national rall international applications that have entered the national s of the reference are not submitted herewith.						
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II.	CONCI a. ⊠ b. □ c. □	information are in the English lang A concise explanation of the relevant that is not in the English language	in (b) of this section, all of the patents, publications or other guage (concise explanation not required). vance of all patents, publications or other information listed						
The Exam be related		ed to the present application. By b	PLICATION(S) co-pending application(s) contain(s) subject matter that may ringing this (these) applications to the Examiner's attention, entiality provisions of 35 U.S.C. §122.						
	Serial N	lo. Filing I	Date Art Unit						
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IV. 🛛	<u>THIS II</u> a.⊠	C.F.R. §1.97(b): (check one box) ng date of a national application other than a continued 1.53(d) (37 C.F.R. §1.97(b)(1)). No fee or statement is							
	b.		of entry of the national stage as set forth in § 1.491 in an R. §1.97(b)(2)). No fee or statement is required.						
	c.	before the mailing date of a first (or statement is required.	before the mailing date of a first Office Action on the merits (37 C.F.R. §1.97(b)(3)). No fee						
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V. 🗖	THIS IDS IS BEING FILED UNDER 37 C.F.R. §1.97(c): (check one box) before the mailing date of any of a Final Office Action under 37 C.F.R. §1.113, a Notice of Allowance under 37 C.F.R. §1.311, or an action that otherwise closes prosecution in the application (See 37 C.F.F. §1.97(c)). a. \(\begin{align*} \) No statement; therefore, charge deposit account 502117 the fee set forth in 37 C.F.R. §1.17(p) See the statement below. No fee is required.						
VI. 🗆	THIS I	IIS IDS IS BEING FILED UNDER 37 C.F.R. §1.97(d): or before payment of the issue fee and is accompanied by the following: a statement under 37 C.F.R. §1.97(e) as provided below; and charge deposit account 502117 the petition fee set forth in §1.17(p).					
VII. [dersigned each ite Patent (of IDS; no item Patent (statement known it filing of some of foreign informa a counte to the r informa a counte making	Office in a counterpart foreign applior of information contained in the Office in a counterpart foreign applint after making reasonable inquiry to any individual designated in 37 of this statement, or a fact that the statement of the items of information contained. Patent Office. As to this information contained in the IDS was cited expart foreign application not more remaining information, the understoon contained in the IDS was cited expart foreign application or, to the reasonable inquiry, no item of in that designated in 37 C.F.R. 1.56(c)	IDS was cited in a communication from a foreign cation not more than three months prior to the filing IDS was cited in a communication from a foreign ication, and to knowledge of the person signing the no item of information contained in the IDS was C.F.R. 1.56(c) more than three months prior to the d in the IDS were cited in a communication from a mation, the undersigned states that each item of in a communication from a foreign Patent Office in than three months prior to the filing of this IDS. As gned hereby states that no item of this remaining in a communication from a foreign Patent Office in knowledge of the person signing the statement after formation contained in the IDS was known to any more than three months prior to the filing of this			
VIII.	PAYMENT OF FEES A check in the amount of is enclosed for the above-identified fee(s). Please charge Deposit Account 502117 in the amount of \$180.00 for the above-indicated fee(s). If Applicant has overlooked any additional fees, or if any overpayment has been made, the Commissioner is hereby authorized to credit or debit Deposit Account 502117. Two Copies of this paper are attached for Deposit Account charges and debits.						
constitu obvious	te statute	ory prior	nces are being cited only in the intact or contain matter which anticipn a combination, to a person of ord	erests of candor and without any admission that they ates the invention or which would render the same nary skill in the art.			
If the Examiner has any questions concerning this IDS, he/she is requested to contact the undersigned. If it is determined that this IDS has been filed under the wrong rule, the PTO is requested to consider this IDS under the proper rule (with a petition if necessary) and charge the appropriate fee to Deposit Account No. 502117. Respectfully submitted, Srikant B. Samavedam							
Custom		NC. er 23125	PTO/SB/09	Joanna G. Chiu Agent for Applicant(s) Reg. No. 43,629 Tel. (512) 996-6839			
Enclosu	res:		PTO/SB/08 References Foreign Search Report Other:				

Pages, Columns, Lines, Where Relevant

				Complete if Known				
				Application Number				
I	NFORMATION	DISCLOSU	RE	Filing Date				
STATEMENT BY APPLICANT			NT	First Named Inventor	Srikanth B. Samavedam			
STATEMENT DI AFFEIDAN				Group Art Unit				
(use as many sheets as necessary)				Examiner Name				
Sheet	1	of	1	Attorney Docket Number	SC13102TP			

Name of Patentee or Applicant

U. S. PATENT DOCUMENTS Publication Date

Cite No. 1

Examiner

Document Number

2003, pp. 347-349.

Examiner Initials*	Cite No. 1	Number -Kind Code ² (if known)		on Date D-YYYY	of Cited Document		Pages, Columns, Lines, where Relevant Pages or Relevant Figures Appear	
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	AC	LEMONDS et al., "Adhesion of Cu and Low-K Dielectric Thin Films With Tungsten Carbide," J. Mater. Res., Vol. 17, No. 6, June 2002, Materials Research Society, pp. 1320-1328.						
	AD	DENG et al., "Reactive Sputtered Titanium Carbide/Nitride and Diamondlike Carbon Coatings," J. Vac. Sci. Technol. A 16(4), Jul/Aug 1998, American Vacuum Society, pp. 2073-2077.						
	AE	PAN et al., "A Low-Temperature Metal-Doping Technique for Engineering the Gate Electrode of Replacement Metal Gate CMOS Transistors," IEEE Electron Device Letters, Vol. 24, No. 9, September						

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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation, if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English Language Translation is attached.

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